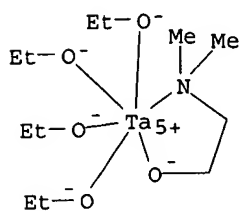


L15 ANSWER 7 OF 12 HCAPLUS COPYRIGHT 2003 ACS on STN  
 AN 2001:225359 HCAPLUS  
 DN 134:246133  
 TI A method and apparatus for integrating a metal nitride film in a semiconductor device  
 IN Narwankar, Pravin; Sahin, Turgut  
 PA Applied Materials, Inc., USA  
 SO Eur. Pat. Appl., 16 pp.  
 CODEN: EPXXDW  
 DT Patent  
 LA English  
 IC ICM H01L021-285  
 CC 76-3 (Electric Phenomena)  
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	EP 1087430	A2	20010328	EP 2000-308405	20000925
	US 6337289	B1	20020108	US 1999-405554	19990924
	SG 83817	A1	20011016	SG 2000-5483	20000922
	TW 477027	B	20020221	TW 2000-89119691	20000922
	JP 2001148380	A2	20010529	JP 2000-290804	20000925
	US 2002055270	A1	20020509	US 2001-2654	20011018
	US 6518203	B2	20030211		
PRAI	US 1999-405554	A	19990924		

AB The present invention describes a method of processing a substrate. According to the present invention a dielec. layer is formed on the substrate. The dielec. layer is then exposed in a 1st chamber to activated N atoms formed in a 2nd chamber to form a N passivated dielec. layer. A metal nitride film is then formed on the N passivated dielec. layer.  
 RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)  
 (for integrating metal nitride film in semiconductor device)

RN 172901-22-3 HCAPLUS  
 CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23)- (9CI) (CA INDEX NAME)



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